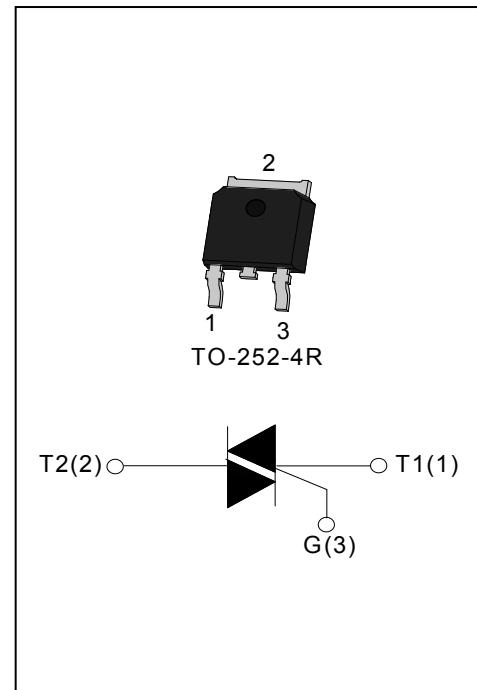


**DESCRIPTION:**

JST134 series triacs with low holding and latching current are especially recommended for use on middle and small resistance type power load. Package TO-252-4R is RoHS compliant. (201/65/EU)

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM} / V_{RRM}	600/800	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40 - 150	°C
Operating junction temperature range	T_j	-40 - 125	°C
Repetitive peak off-state voltage($T_j = 25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage($T_j = 25^\circ\text{C}$)	V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current ($T_c = 110^\circ\text{C}$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)	I_{TSM}	30	A
I^2t value for fusing ($t_p = 10\text{ms}$)	I^2t	4.5	A^2s
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	I - II - III IV	50 10	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	2	A

Average gate power dissipation	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value			Unit
				T	D	E	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX	5	5	10	mA
		IV		5	10	25	
V_{GT}	ALL	MAX		1.3			V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN	0.2			V
I_L	$I_G=1.2I_{GT}$	I - III-IV	MAX	8	10	20	mA
		II		12	15	35	
I_H	$I_T=100\text{mA}$	MAX		5	10	20	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$	MIN		20	50	100	V/ μs
(dV/dt)c	(dI/dt)c=1.1A/ms $T_j=125^\circ\text{C}$	MIN		0.5	1	5	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=5\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.7	V
I_{DRM}		$T_j=25^\circ\text{C}$	5	μA
I_{RRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=125^\circ\text{C}$	0.5	mA

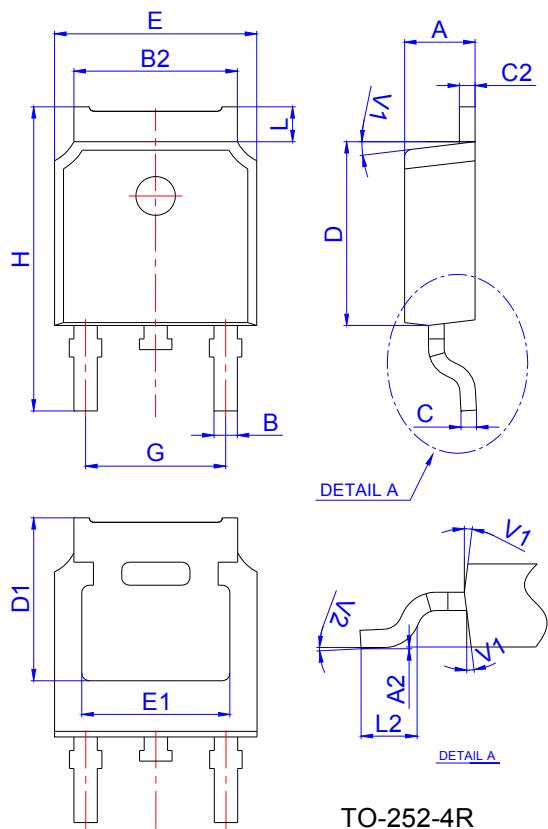
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252-4R	3.7	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient		70	

ORDERING INFORMATION

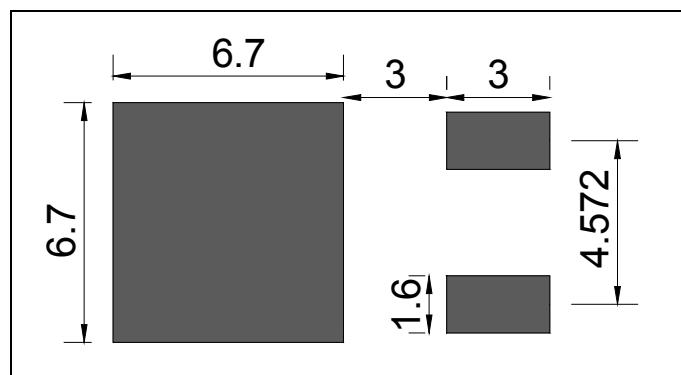
J	ST	134	K	-600	D
JieJie Microelectronics Co.,Ltd					T:IGT1-3≤5mA IGT4≤5mA D:IGT1-3≤5mA IGT4≤10mA E:IGT1-3≤10mA IGT4≤25mA
					600:V _{DRM} /V _{RRM} ≥600V 800:V _{DRM} /V _{RRM} ≥800V
					K:TO-252-4R KTR:TO-252-4R(Tape&Reel)

PACKAGE MECHANICAL DATA

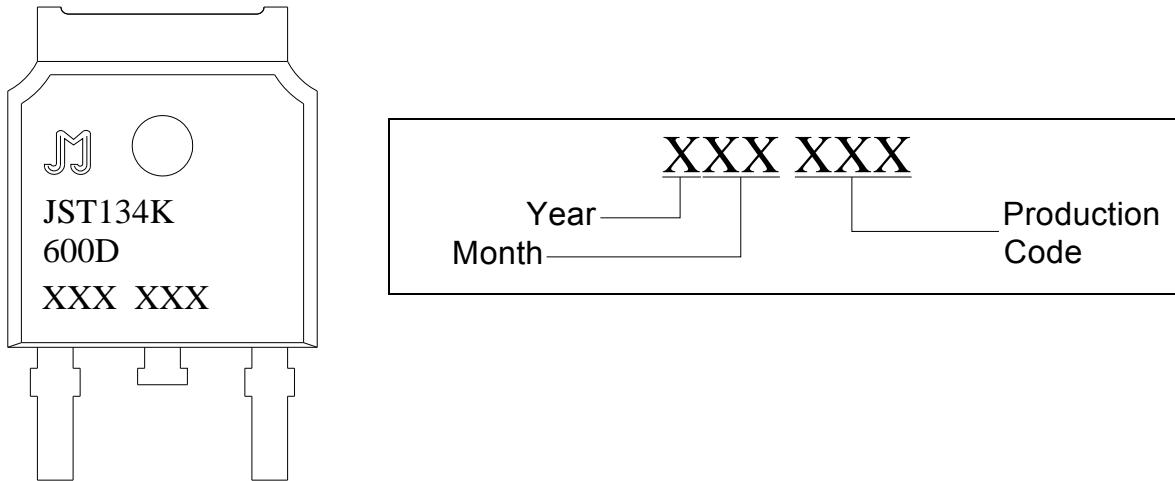


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

FOOTPRINT-TO-252-4R (dimensions in mm)



MARKING



PACKAGE INFORMATION

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-252-4R	TUBE	80	4,000	32,000
PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-252-4R	TAPING	2,500	25,000	13 inch

FIG.1: Maximum power dissipation versus RMS on-state current

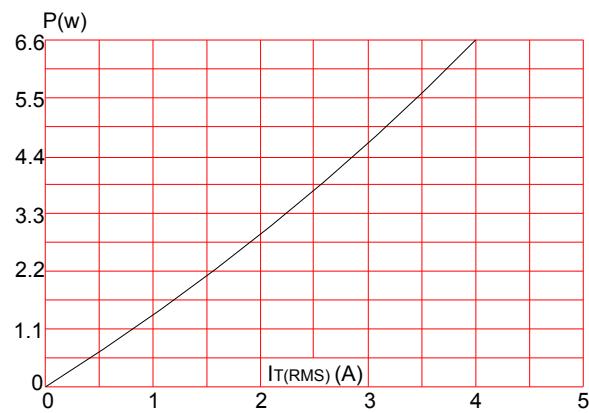


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm) (full cycle)

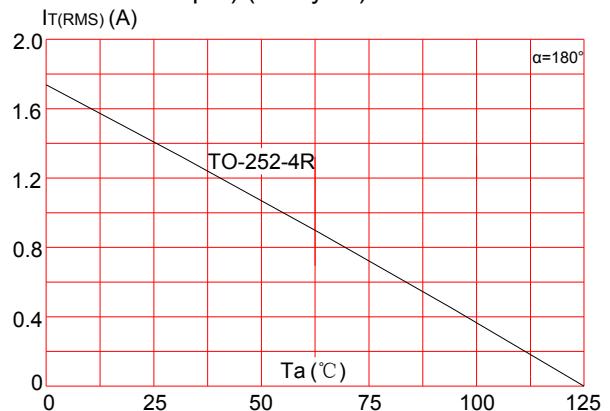


FIG.3: Surge peak on-state current versus number of cycles

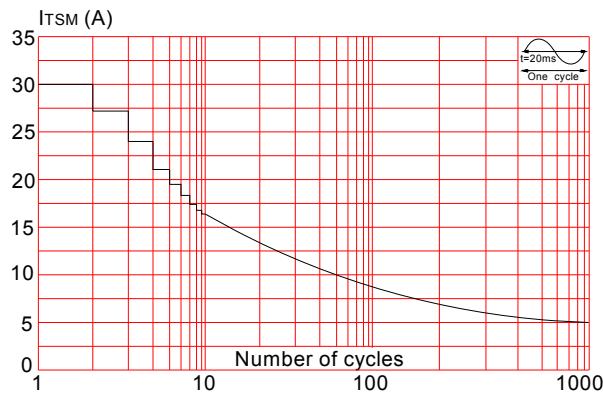


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t (I - II - III: $dI/dt < 50\text{A}/\mu\text{s}$; IV: $dI/dt < 10\text{A}/\mu\text{s}$)

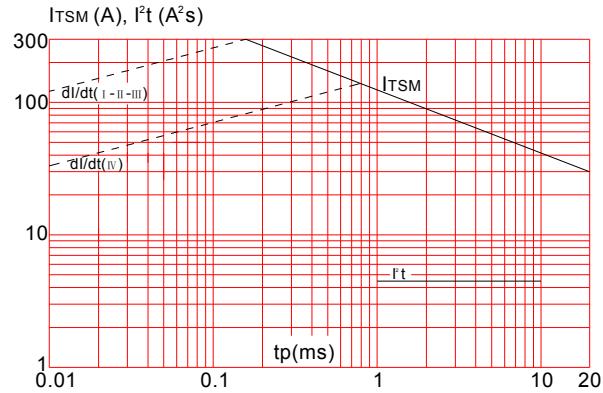


FIG.7: Relative variations of holding current versus junction temperature

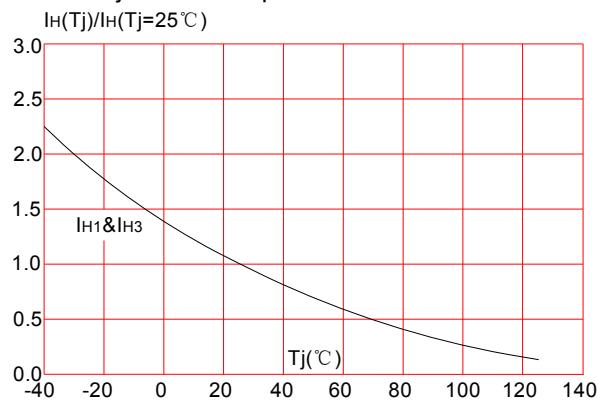


FIG.4: On-state characteristics (maximum values)

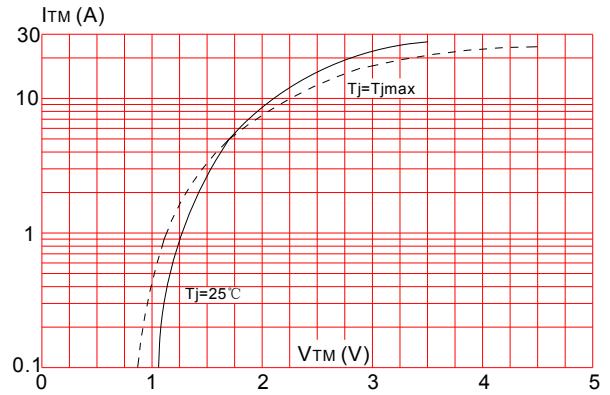


FIG.6: Relative variations of gate trigger current versus junction temperature

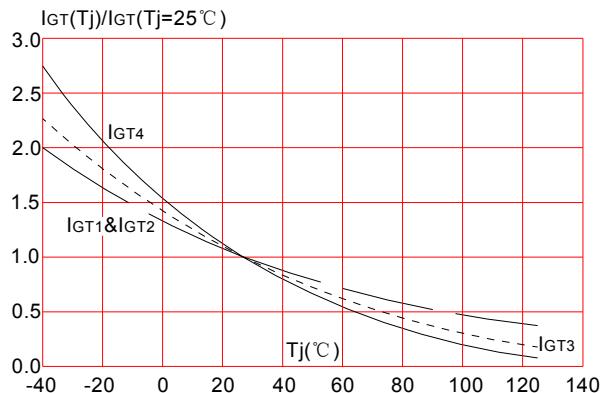
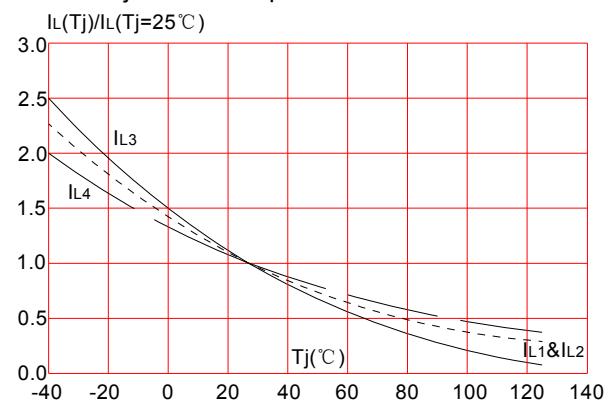
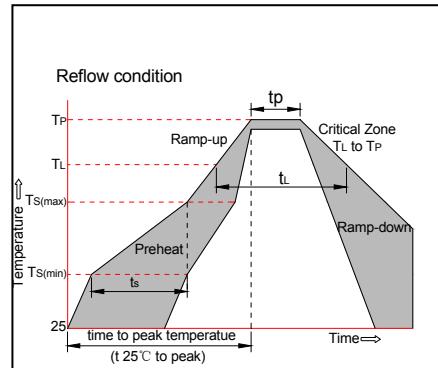


FIG.8: Relative variations of latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(\min)}$)	+150 °C
	-Temperature Max($T_{s(\max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L)to peak)		3 °C/sec. Max
$T_{s(\max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217 °C
	-Temperature(t_p)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260 °C



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